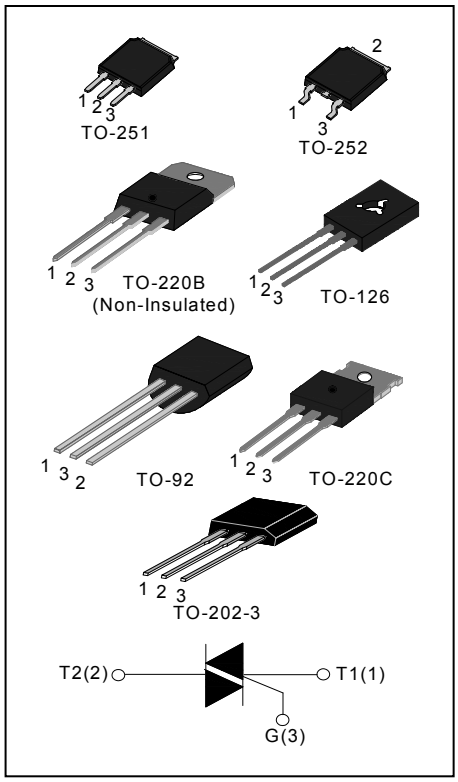
DESCRIPTION:

YR134 series triacs with low holding and latching current are especially recommended for use on middle and small resistance type power load.



MAIN FEATURES

Symbol	Value	Unit
$I_{T(RMS)}$	2	A
V_{DRM} /V_{RRM}	600	V

ABSOLUTE MAXIMUM RATINGS

Parameter		Symbol	Value	Unit
Storage junction temperature range		T_{stg}	-40 - 150	℃
Operating junction temperature range		T_j	-40 - 125	℃
Repetitive peak off-state voltage(T_j=25℃)		V_{DRM}	600	V
Repetitive peak reverse voltage(T_j=25℃)		V_{RRM}	600	V
Non repetitive surge peak Off-state voltage		V_{DSM}	V_{DRM} + 100	V
Non repetitive peak reverse voltage		V_{RSM}	V_{RRM} + 100	V
RMS on-state current	TO-251 TO-252 (T_C=110℃)	$I_{T(RMS)}$	2	A
	TO-220B(Non-Ins)/ TO-220C(T_C=103℃)			
	TO-202-3 (T_C=80℃)			
	TO-126 (T_C=100℃)			
	TO-92 (T_C=70℃)			

Non repetitive surge peak on-state current (full cycle, F=50Hz)		I_{TSM}	12	A
I^2t value for fusing (tp =10ms)		I^2t	3.1	A^2s
Critical rate of rise of on-state current (I_G =2×I_{GT})	Ⅰ-Ⅱ-Ⅲ	dI/dt	50	A/μs
	Ⅳ		10	
Peak gate current		I_{GM}	2	A
Average gate power dissipation		$P_{G(AV)}$	0.5	W
Peak gate power		P_{GM}	5	W

ELECTRICAL CHARACTERISTICS (T_j=25℃ unless otherwise specified)

Symbol	Test Condition	Quadrant		Value			Unit
				T	D	E	
I_{GT}	V_D=12V R_L=33Ω	Ⅰ-Ⅱ-Ⅲ	MAX	5	5	10	mA
		Ⅳ		5	10	25	
V_{GT}		ALL	MAX	1.3			V
V_{GD}	V_D=V_{DRM} T_j=125℃ R_L=3.3KΩ	ALL	MIN	0.2			V
I_L	I_G=1.2I_{GT}	Ⅰ-Ⅲ-Ⅳ	MAX	8	10	20	mA
		Ⅱ		12	15	35	
I_H	I_T=100mA		MAX	5	10	20	mA
dV/dt	V_D=2/3V_{DRM} Gate Open T_j=125℃		MIN	20	50	100	V/μs
(dV/dt)c	(dI/dt)c=1.1A/ms T_j=125℃		MIN	0.5	1	5	V/μs

STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX)	Unit
V_{TM}	I_{TM}=5A tp=380μs	T_j=25℃	1.7	V
I_{DRM}	V_D=V_{DRM} V_R=V_{RRM}	T_j=25℃	5	μA
I_{RRM}		T_j=125℃	0.5	mA

THERMAL RESISTANCES

Symbol	Parameter		Value	Unit
$R_{th(j-c)}$	junction to case(AC)	TO-251-4R/ TO-252-4R	3.7	℃/W
		TO-220B(Non-Ins)/ TO-220C	3.1	
		TO-202-3	4.5	
		TO-126	4.1	
		TO-92	11.2	

FIG.1: Maximum power dissipation versus RMS on-state current

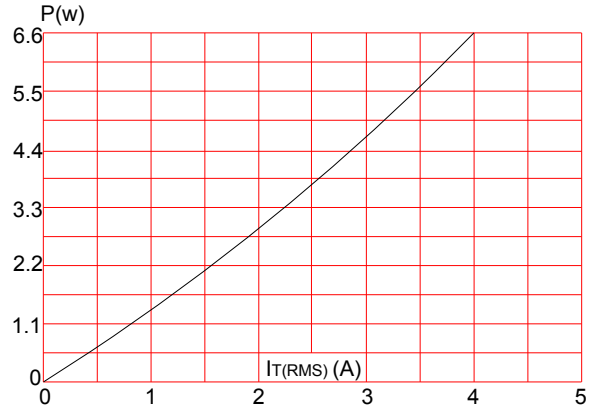


FIG.2: RMS on-state current versus case temperature

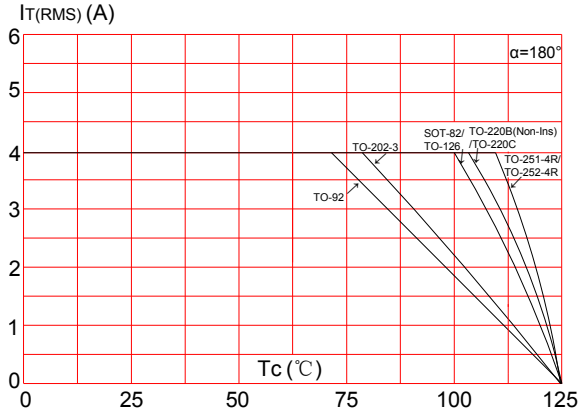


FIG.3: Surge peak on-state current versus number of cycles

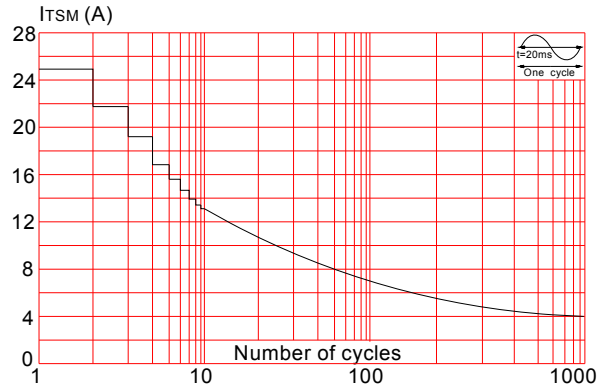


FIG.4: On-state characteristics (maximum values)

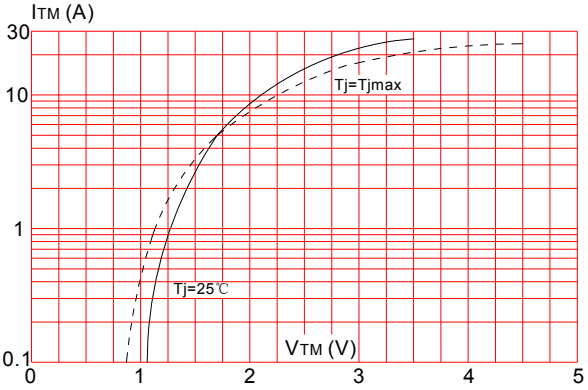


FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width tp<20ms and corresponding value of I^2t (Ⅰ-Ⅱ-Ⅲ:dI/dt < 50A/μs; Ⅳ:dI/dt < 10A/μs)

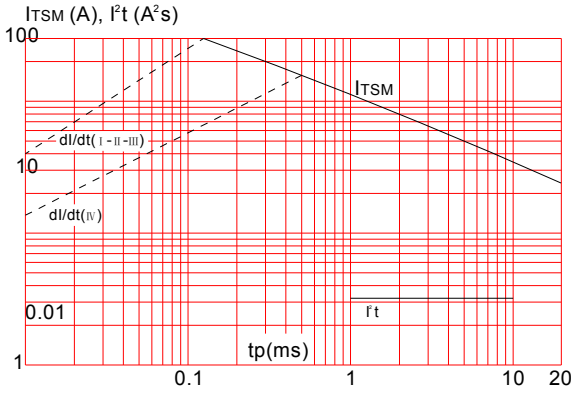


FIG.6: Relative variations of gate trigger current versus junction temperature

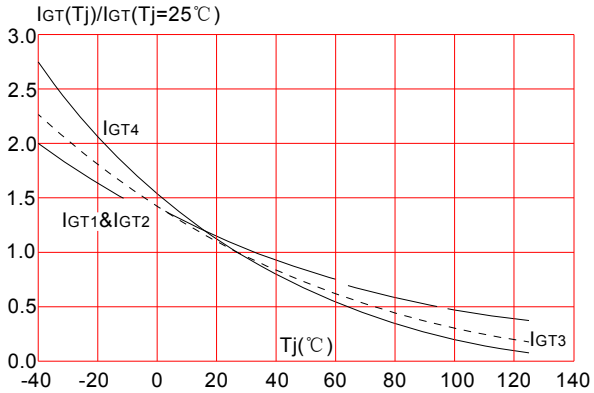


FIG.7: Relative variations of holding current versus junction temperature

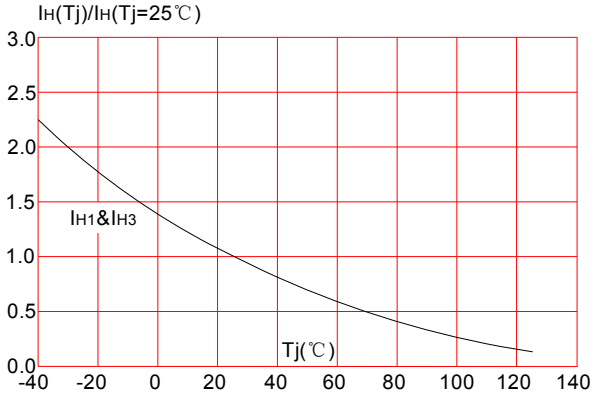


FIG.8: Relative variations of latching current versus junction temperature